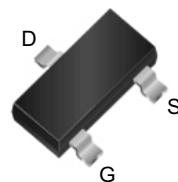


WNM5002

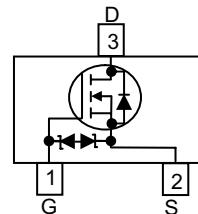
[Http://www.willsemi.com](http://www.willsemi.com)

Small Signal N-Channel, 50V, 0.50A, MOSFET

V_{DS} (V)	Typical R_{DS(on)} (Ω)
50	1.3@ V _{GS} =10V
	1.4@ V _{GS} =4.5V
	2.1@ V _{GS} =2.5V
ESD Rating: 2000V HBM	



SOT-23



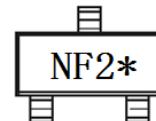
Pin configuration (Top view)

Descriptions

The WNM5002 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R_{DS(ON)} with low gate charge. This device is suitable for use in small signal switch. Standard Product WNM5002 is Pb-free and Halogen-free.

Features

- Trench Technology
- Supper high density cell design
- Excellent ON resistance for higher DC current
- HBM ESD protection >2 kV
- Small package SOT-23



NF2 = Device Code

* = Month (A~Z)

Marking

Applications

- Driver: Relay, Solenoid, Lamps,Hammers etc.
- Power supply converters circuit
- Load/Power Switching for potable device

Order information

Device	Package	Shipping
WNM5002-3/TR	SOT-23	3000/Reel&Tape

Absolute Maximum ratings

Parameter	Symbol	10 S	Steady State	Unit
Drain-Source Voltage	V _{DS}	50		V
Gate-Source Voltage	V _{GS}	±20		
Continuous Drain Current ^{a d}	T _A =25°C	I _D	0.50	A
	T _A =70°C		0.40	
Maximum Power Dissipation ^{a d}	T _A =25°C	P _D	0.69	W
	T _A =70°C		0.44	
Continuous Drain Current ^{b d}	T _A =25°C	I _D	0.47	A
	T _A =70°C		0.38	
Maximum Power Dissipation ^{b d}	T _A =25°C	P _D	0.60	W
	T _A =70°C		0.39	
Pulsed Drain Current ^c	I _{DM}		1.2	A
Operating Junction Temperature	T _J		-55 to 150	°C
Lead Temperature	T _L		260	°C
Storage Temperature Range	T _{stg}		-55 to 150	°C

Thermal resistance ratings

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ^a	t ≤ 10 s	R _{θJA}	140	180
	Steady State		176	
Junction-to-Ambient Thermal Resistance ^b	t ≤ 10 s	R _{θJA}	165	205
	Steady State		198	
Junction-to-Case Thermal Resistance	R _{θJC}	100	120	

a Surface mounted on FR-4 Board using 1 square inch pad size, 1oz copper

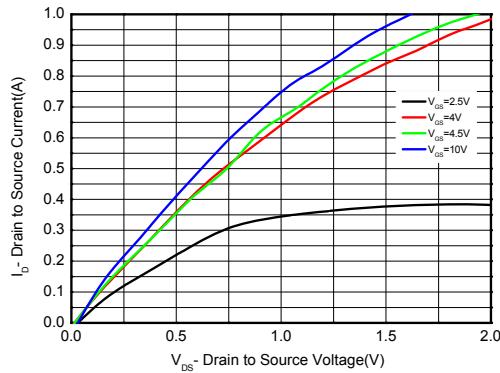
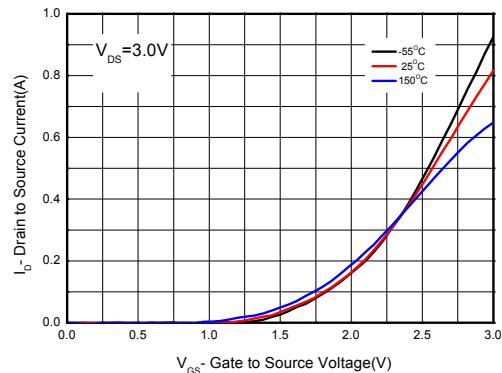
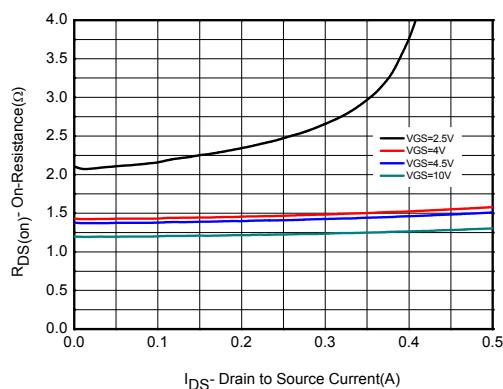
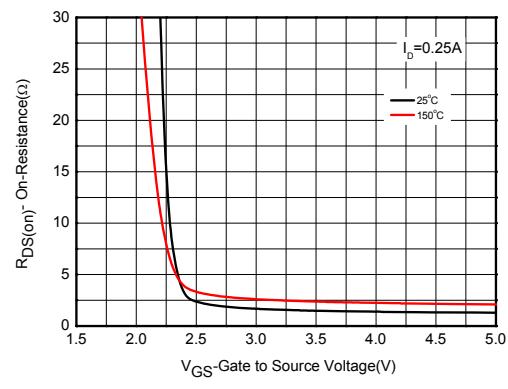
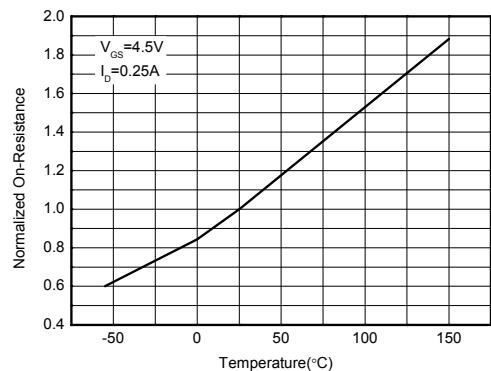
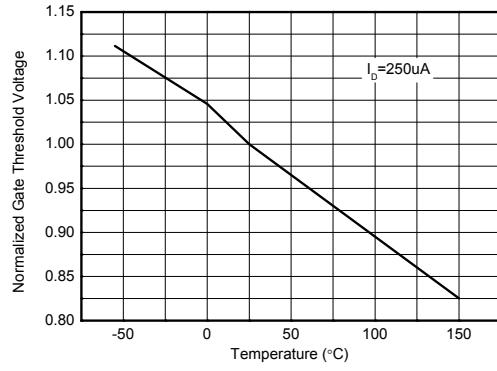
b Surface mounted on FR-4 board using minimum pad size, 1oz copper

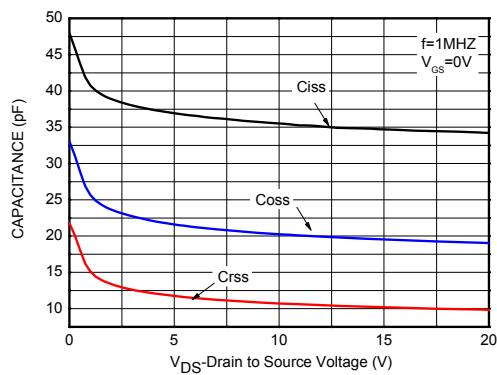
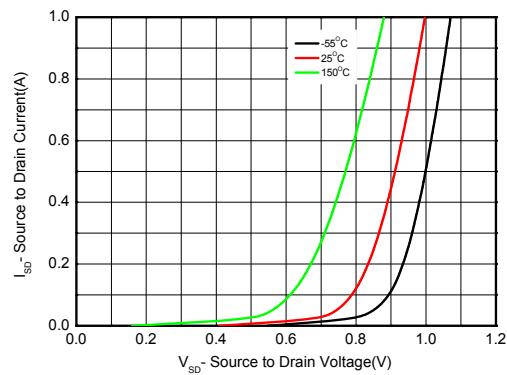
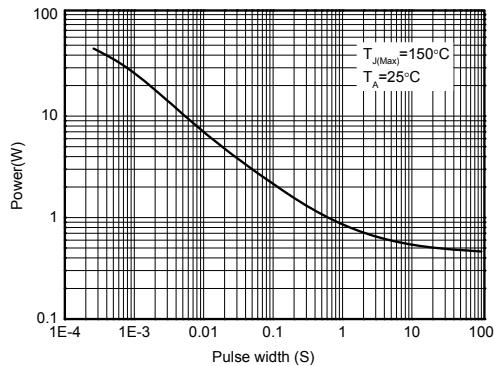
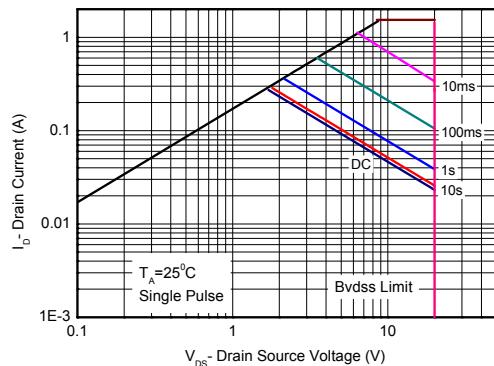
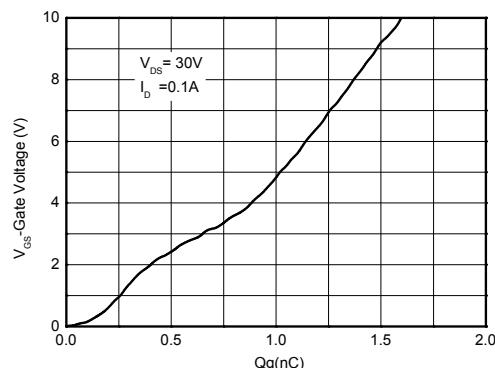
c Pulse width<380μs, Duty Cycle<2%

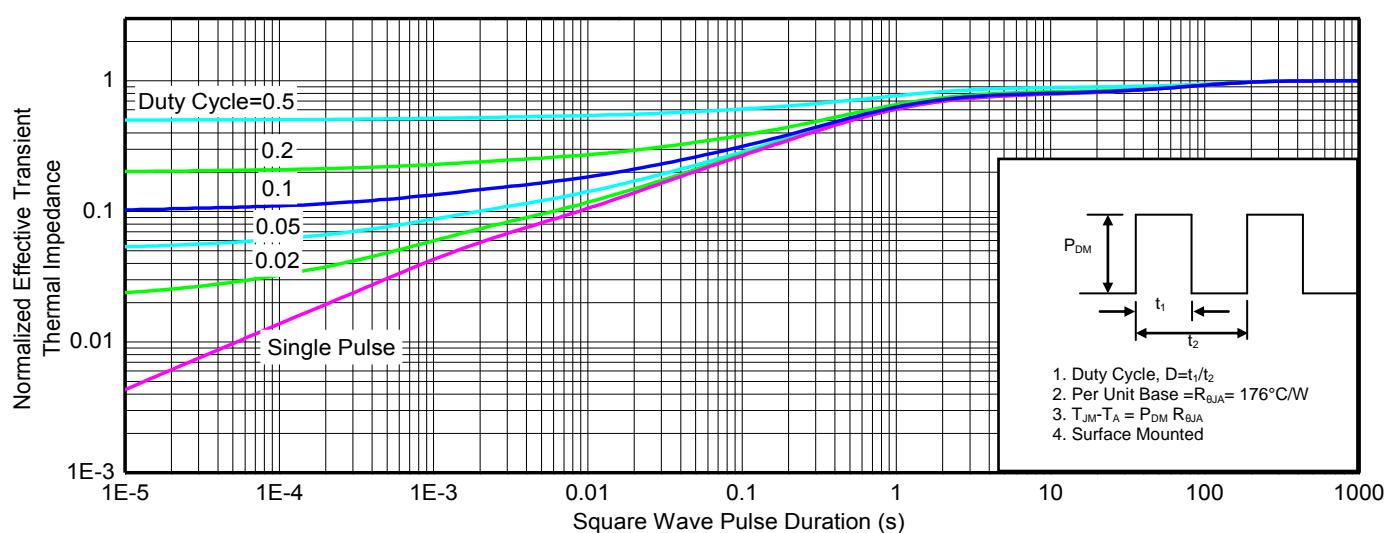
d Maximum junction temperature T_J=150°C.

Electronics Characteristics (Ta=25°C, unless otherwise noted)

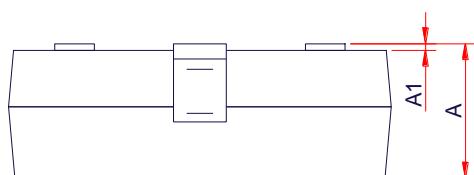
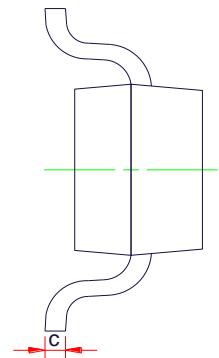
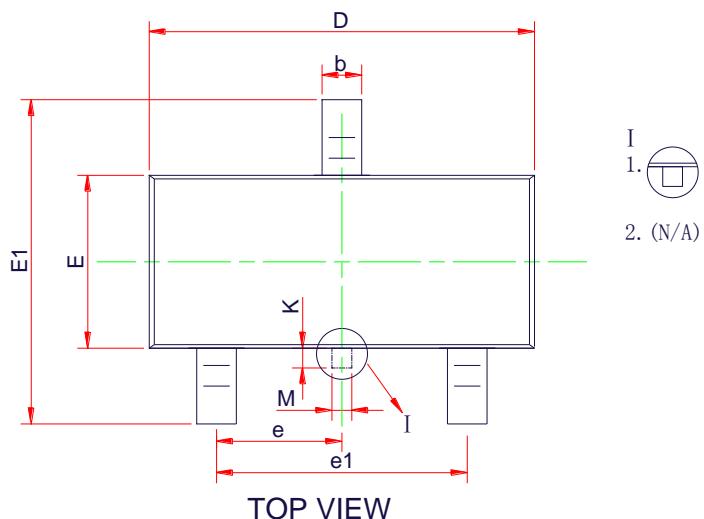
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	50			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 50V, V_{GS} = 0V$			1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 5	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	0.8	1.0	1.5	V
Drain-to-source On-resistance ^{b, c}	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.45A$		1.3	3	Ω
		$V_{GS} = 4.5V, I_D = 0.25A$		1.4	4	
		$V_{GS} = 4.0V, I_D = 0.25A$		1.5	4	
		$V_{GS} = 2.5V, I_D = 0.01A$		2.1	6	
Forward Trans conductance	g_{fs}	$V_{DS} = 15V, I_D = 0.1A$		0.5		S
CAPACITANCES, CHARGES						
Input Capacitance	C_{ISS}	$V_{GS} = 0V,$ $F = 1.0 \text{ MHz},$ $V_{DS} = 5V$		36		pF
Output Capacitance	C_{OSS}			22		
Reverse Transfer Capacitance	C_{RSS}			12		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10V,$ $V_{DD} = 30V,$ $I_D = 0.1A$		1.6		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.25		
Gate-to-Source Charge	Q_{GS}			0.4		
Gate-to-Drain Charge	Q_{GD}			0.45		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$td(ON)$	$V_{GS} = 5V,$ $V_{DD} = 5V,$ $R_L = 500\Omega,$ $R_G = 10\Omega, I_D = 10mA$		8.6		ns
Rise Time	tr			4		
Turn-Off Delay Time	$td(OFF)$			23.8		
Fall Time	tf			14.2		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 0.25A$		0.8	1.5	V

Typical Characteristics (Ta=25°C, unless otherwise noted)

Output characteristics

Transfer characteristics

On-Resistance vs. Drain current

On-Resistance vs. Gate-to-Source voltage

On-Resistance vs. Junction temperature

Threshold voltage vs. Temperature


Capacitance

Body diode forward voltage

Single pulse power

Safe operating power

Gate charge Characteristics

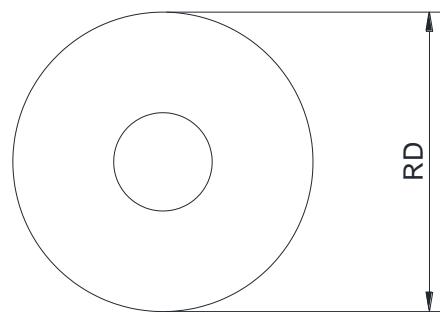
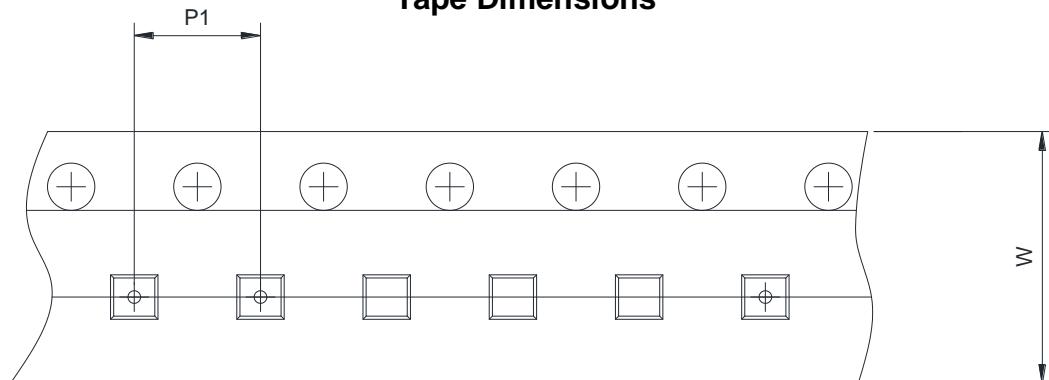
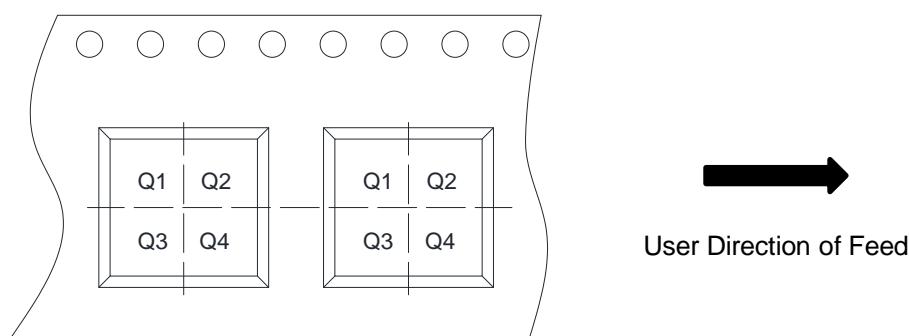


Transient thermal response (Junction-to-Ambient)

PACKAGE OUTLINE DIMENSIONS
SOT-23


SIDE VIEW

Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.89	1.10	1.30
A1	0.00	-	0.10
b	0.30	0.43	0.55
c	0.05	-	0.20
D	2.70	2.90	3.10
E	1.15	1.33	1.50
E1	2.10	2.40	2.70
e	0.95 Typ.		
e1	1.70	1.90	2.10
K	0.00	-	0.25
M	0.10	0.15	0.25

TAPE AND REEL INFORMATION
Reel Dimensions

Tape Dimensions

Quadrant Assignments For PIN1 Orientation In Tape


RD	Reel Dimension	<input checked="" type="checkbox"/> 7inch <input type="checkbox"/> 13inch
W	Overall width of the carrier tape	<input checked="" type="checkbox"/> 8mm <input type="checkbox"/> 12mm <input type="checkbox"/> 16mm
P1	Pitch between successive cavity centers	<input type="checkbox"/> 2mm <input checked="" type="checkbox"/> 4mm <input type="checkbox"/> 8mm
Pin1	Pin1 Quadrant	<input type="checkbox"/> Q1 <input type="checkbox"/> Q2 <input checked="" type="checkbox"/> Q3 <input type="checkbox"/> Q4